

PATENT
740756-1881

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

GAU 2815
#1/a
D. Scott
3/13/01

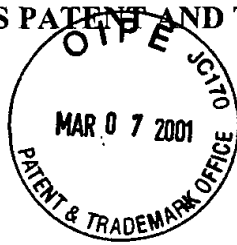
In re PATENT application of:

Hongyong ZHANG et al.

Application No.: 09/190,618

Filed: November 12, 1998

For: SEMICONDUCTOR DEVICE
AND METHOD FOR
FABRICATING THE SAME



Art Unit: 2815

Examiner: E. Lee

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on 3/5/01

Deborah J. Zorn

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

March 5, 2001 (Monday)

Dear Sir:

In response to the Examiner's non-final Office Action mailed October 3, 2000, the period for responding having been extended Two (2) months, please consider the following amendments and remarks in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claims 26-33 without prejudice to or disclaimer of the subject matter disclosed therein.

Please amend claim 19 as follows:

Q1 Sub C7 19. (Amended) A semiconductor device including at least one thin film transistor, said thin film transistor comprising:

- a gate electrode;
- a gate insulating film adjacent to the gate electrode; and
- a semiconductor film adjacent to said gate insulating film wherein said semiconductor film includes a channel forming region, a pair of first regions containing an impurity for giving